## Solution Processable Si/Ge Heterostructure NWs Enabling Anode

## Mass Reduction for Practical Full-cell Li-ion Batteries

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## SUPPLEMENTARY MATERIALS



**Figure S1.** Quantitative EDX estimation of the % weight of Si, Ge and Sn from multiple areas of the anode. The mean value was obtained (Sn:Si:Ge weight % ratio is: 18:50:32).



**Figure S2.** Histograms representing NW diameter distribution of Si and Ge segment in hSG NWs. Each distribution was obtained by direct counting method, measuring the diameters for 200 NWs from SEM images.



**Figure S3.** (a) HAADF-STEM image of hSG NW viewed from <110> orientation. (b) Highresolution image, heterointerface highlighted by the green overlay, showing defect across the Si-Ge segment. (c) Atomic-resolution image of the heterointerface indicating SF marked by the white dashed lines. Insets are (i) FFT spots and (ii) IFFT image corresponding to the regions of SF.



**Figure S4**. Voltage - Specific capacity profile of Si NWs (slurry) for 1<sup>st</sup> and 50<sup>th</sup> cycle at 0.2 C.



Figure S5. Fitting circuit used for EIS analysis.

	R <sub>s</sub> (ohm)	R <sub>cT</sub> (ohm)	
1 <sup>st</sup> cyc	19.29	47.98	
50 <sup>th</sup> cyc	19.96	5.17	

Table S1. Tabulation of  $R_s$  and  $R_{ct}$  values of hSG NWs after  $1^{st}$  and  $50^{th}$  cycle.



**Figure S6**. (a) Rate capability test and (b) corresponding voltage – specific capacity plot of hSG NWs at various C-rates.



**Figure S7**. TEM analysis of the hSG anode at the 5<sup>th</sup> cycle (a) low magnification TEM image of the Sn, Si and Ge segments. (b) high magnification of Si and Ge segments. (c) Diffraction pattern of b with both segments now amorphous.



**Figure S8.** Comparison of dQ/dV curve of hSG and Si NWs at 5<sup>th</sup> , 25<sup>th</sup> and 50<sup>th</sup> cycle (at 0.2 C).



**Figure S9.** Raman spectroscopy analysis of hSG NWs before cycling (pristine), after 5<sup>th</sup> and 25<sup>th</sup> cycle.

Anode material	Active mass (mg cm <sup>-2</sup> )	Total anode mass (mg cm <sup>-2</sup> )	Anode mass reduction (%)
Graphite	4.56	5.07	50.7%
hSG	1.5	2.5	

**Table S2.** Anode mass reduction calculation of hSG vs. standard graphite anode using P/N ratio of 1.18. The total anode mass consists of active material, conductive agent and binder weight as well. For graphite anode total mass calculation, a standard slurry composition of 90 % graphite, 5 % conductive agent and 5 % binder was used. The theoretical capacity of graphite used was 372 mAh g<sup>-1</sup>.



**Figure S10**. Voltage – specific capacity plot of hSG - NMC811 cell after 1<sup>st</sup> and 50<sup>th</sup> cycled at 0.2 C.